

OPA8760EDD

Infrared LED Chip

High Speed

GaAlAs/GaAlAs

1. Material Substrate GaAlAs (N Type) Removed
Epitaxial Layer GaAlAs (P/N Type)

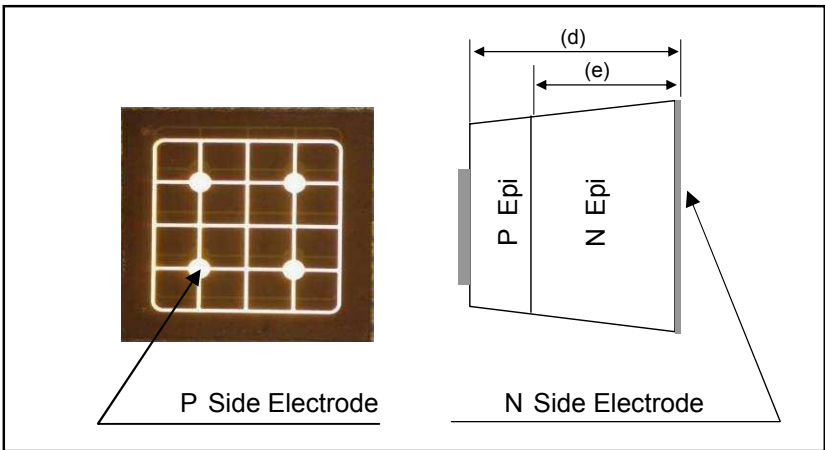
2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10mA
	$V_{F(2)}$			1.5	V	IF=250mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O		11.0		mW	IF=250mA
Wavelength	λ_P		870		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	T_r		15		ns	
Fall Time	T_f		6.3		ns	

※ Note : LED chip is mounted on TO-18 gold header without resin coating.

- 4. Mechanical Data**
- (a) Emission Area ----- 58.1mil x 58.1mil
 - (b) Bottom Area ----- 59.1mil x 59.1mil
 - (c) Bonding Pad ----- 128um
 - (d) Chip Thickness ----- 7mil
 - (e) Junction Height ----- 6.4mil



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